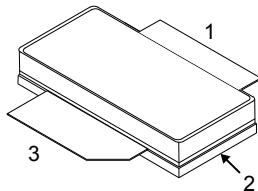


180 W, 28 V, 1.3 to 1.7 GHz RF power LDMOS transistor



B2

Pin connection	
Pin	Connection
1	Gate
2	Source (bottom side)
3	Drain

Features

Order code	Frequency	V _{DD}	P _{OUT}	Gain	Efficiency
RF2L16180CF2	1470 MHz	28 V	180 W	17.5 dB	56%

- High efficiency and linear gain operations
- Integrated ESD protection
- Internal input matching for ease of use
- Large positive and negative gate-source voltage range for improved class C operation
- Excellent thermal stability, low HCI drift
- In compliance with the european directive 2002/95/EC

Applications

- Base stations
- L-band radars
- Industrial, scientific and medical (ISM)

Description

The **RF2L16180CF2** is a 180 W internally matched LDMOS transistor designed for multicarrier WCDMA/PCS/DCS/LTE base stations and ISM applications in the frequency range from 1.3 to 1.7 GHz. It can be used in class AB, B or C for all typical modulation formats.



Product status link
RF2L16180CF2

Product summary	
Order code	RF2L16180CF2
Marking	2L16180
Package	B2
Packing	Tape and reel 13"
Base/Bulk quantity	120/120

1 Electrical ratings

Table 1. Absolute maximum ratings ($T_C = 25\text{ °C}$)

Symbol	Parameter	Value	Unit
$V_{(BR)DSS}$	Drain-source voltage	65	V
V_{GS}	Gate-source voltage	-6 to 10	V
V_{DD}	Maximum operating voltage	32	V
T_{STG}	Storage temperature range	-65 to 150	°C
T_J	Maximum junction temperature	200	°C

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thJC}^{(1)}$	Thermal resistance, junction-to-case	0.38	°C/W

1. $T_C = 85\text{ °C}$, $T_J = 200\text{ °C}$, DC test.

Table 3. ESD protection

Symbol	Parameter	Class
HBM	Human body model (according to ANSI/ESDA/JEDEC JS001-2017)	0B
CDM	Charge device model (according to ANSI/ESDA/JEDEC JS-002-2014)	C3

2 Electrical characteristics

$T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 100\text{ }\mu\text{A}$	65			V
I_{DSS}	Zero-gate voltage drain leakage current	$V_{GS} = 0\text{ V}$, $V_{DS} = 28\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 50\text{ V}$				
I_{GSS}	Gate-body leakage current	$V_{GS} = -6/10\text{ V}$, $V_{DS} = 0\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = 28\text{ V}$, $I_D = 600\text{ }\mu\text{A}$	1.75		2.50	V
$V_{GS(Q)}$	Gate quiescent voltage	$V_{DS} = 1\text{ V}$, $I_D = 800\text{ mA}$	2		4	V
$V_{DS(on)}$	Static drain-source on-voltage	$V_{GS} = 10\text{ V}$, $I_D = 5\text{ A}$			0.5	V
$I_{DS(on)}$	Static drain-source on-current	$V_{GS} = 10\text{ V}$, $V_{DS} = 100\text{ mV}$			2.5	A
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $V_{DS} = 100\text{ mV}$			1	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
f	Frequency		1300		1700	MHz
P_{OUT}	Output power	f = 1470 MHz, at 1dB compression point		180		W
G_{PS}	Power gain			17.5		dB
η_D	Drain efficiency			56		%
VSWR	Load mismatch	$P_{OUT} = 180\text{ W}$, all phases			10:1	

Note: $V_{DD} = 28\text{ V}$, $I_{DQ} = 800\text{ mA}$, Pulsed CW, pulse width = 10 μs , duty cycle = 12%.

3 Typical performances

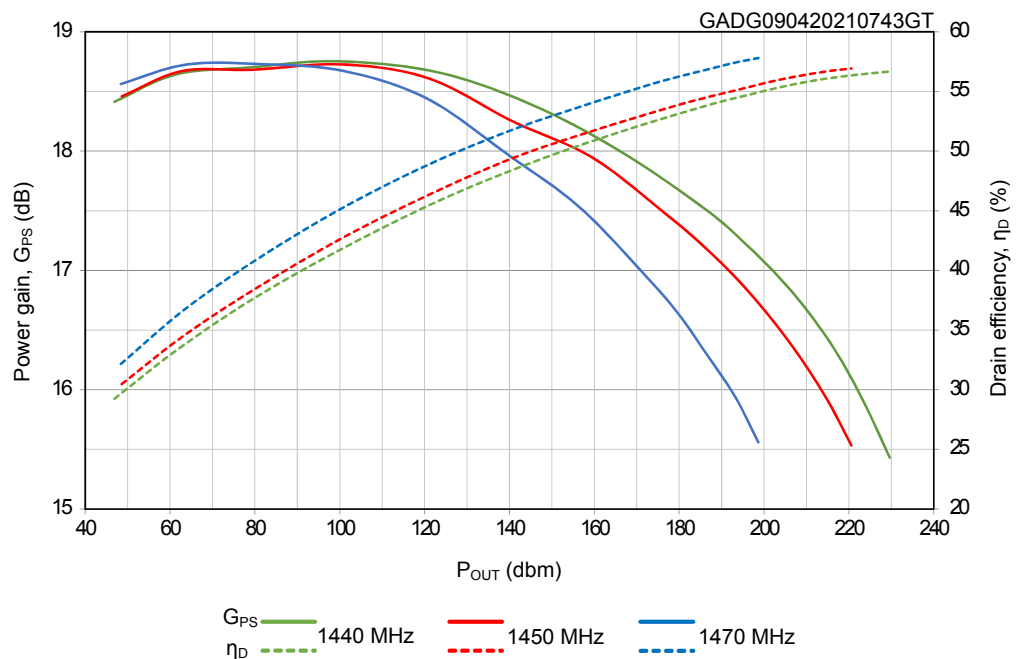
3.1 Pulsed CW performance

Table 6. Typical performance vs frequency

f (MHz)	G _{PS} @P _{1dB} (dB)	P _{1dB} (W)	P _{3dB} (W)	η _D @P _{3dB} (%)
1440	17.6	182	227	56.6
1450	17.4	177	222	57
1470	17.2	165	201	58

Note: $V_{DD} = 28$ Volts, $I_{DQ} = 800$ mA, pulsed CW, pulse width = 10 μs, duty cycle = 12%

Figure 1. Power gain and drain efficiency vs output power (1440 to 1470 MHz)



3.2 WCDMA performance

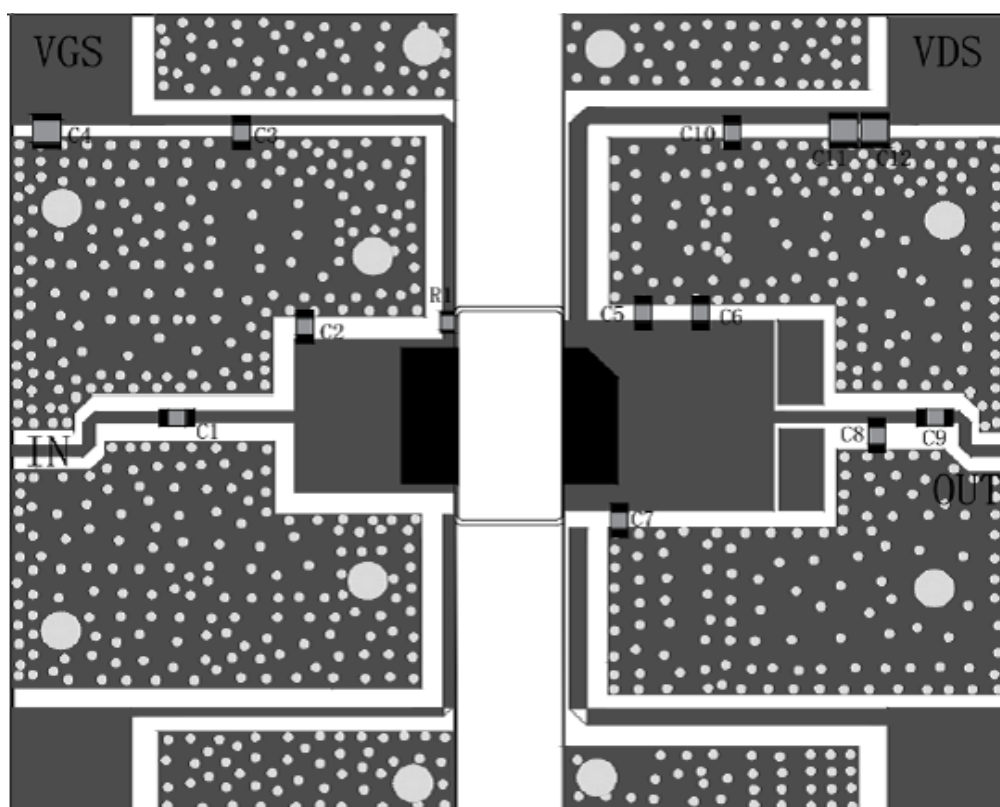
Table 7. Typical single-carrier W-CDMA performance (P_{OUT,avg} = 45 dBm)

f (MHz)	G _{PS} (dB)	η _D (%)	PAR out (dB)	ACPR1 low (dBc)	ACPR1 high (dBc)	ACPR2 low (dBc)	ACPR2 high (dBc)
1440	18.2	26.4	8.10	-30.7	-30.6	-54.0	-53.0
1450	17.6	27.0	7.91	-31.3	-31.7	-53.0	-54.0
1470	18.2	28.6	7.86	-31.3	-30.6	-53.2	-51.5

Note: $V_{DD} = 28$ V, $I_{DQ} = 600$ mA, WCDMA signal: 3GPP test model 1; 1 to 64 DPCH; channel bandwidth = 3.84 MHz, PAR = 10 dB at 0.01 % probability on CCDF. Test performed at 45 dBm average output power level.

4 Test circuits

Figure 2. Test circuit layout (1440 to 1470 MHz)



GADG100920181336IG

Figure 3. Test circuit photo

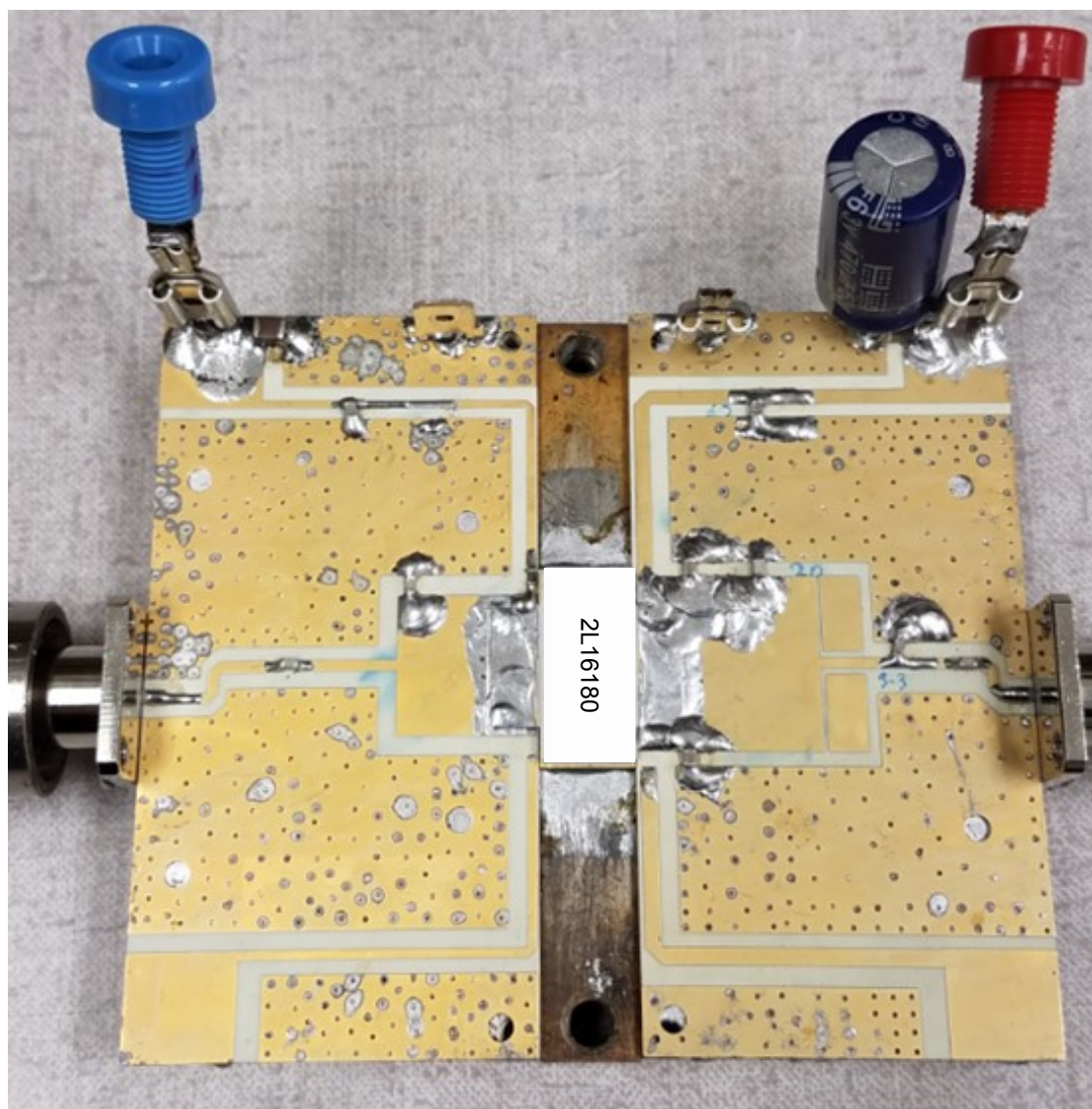


Table 8. Components list

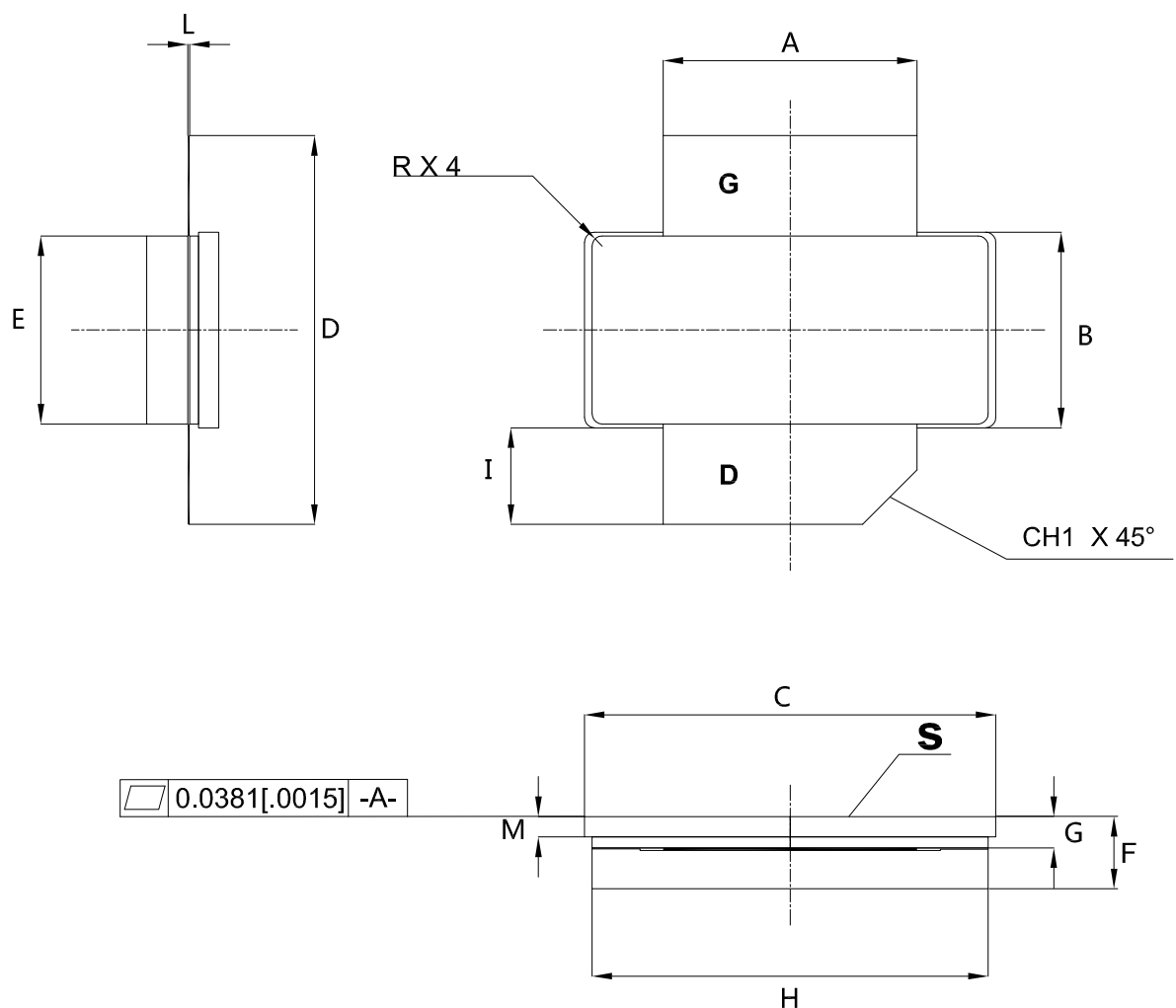
Component	Value	Size	Reference
Q1	RF2L16180CF2		
C1	30 pF	0805	ATC600F 300
C2	2.2 pF	0805	ATC600F 2R2
C3, C10	27 pF	0805	ATC600F 270
R1	10 Ω	0603	Digi-Key P10ECT-ND
C4, C11, C12	10 uF	1210	Murata GRM32DF51H106
C5	4.7 pF	0805	ATC600F 4R7
C6	3.9 pF	0805	ATC600F 3R9
C7	5.6 pF	0805	ATC600F 5R6
C8	3.0 pF	0805	ATC600F 3R0
C9	33 pF	0805	ATC600F 330
PCB	0.508 mm (0.020") thick, $\epsilon_r = 3.48$, Rogers RO4350B, 1 oz. copper		

5 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

5.1 B2 package information

Figure 4. B2 package outline



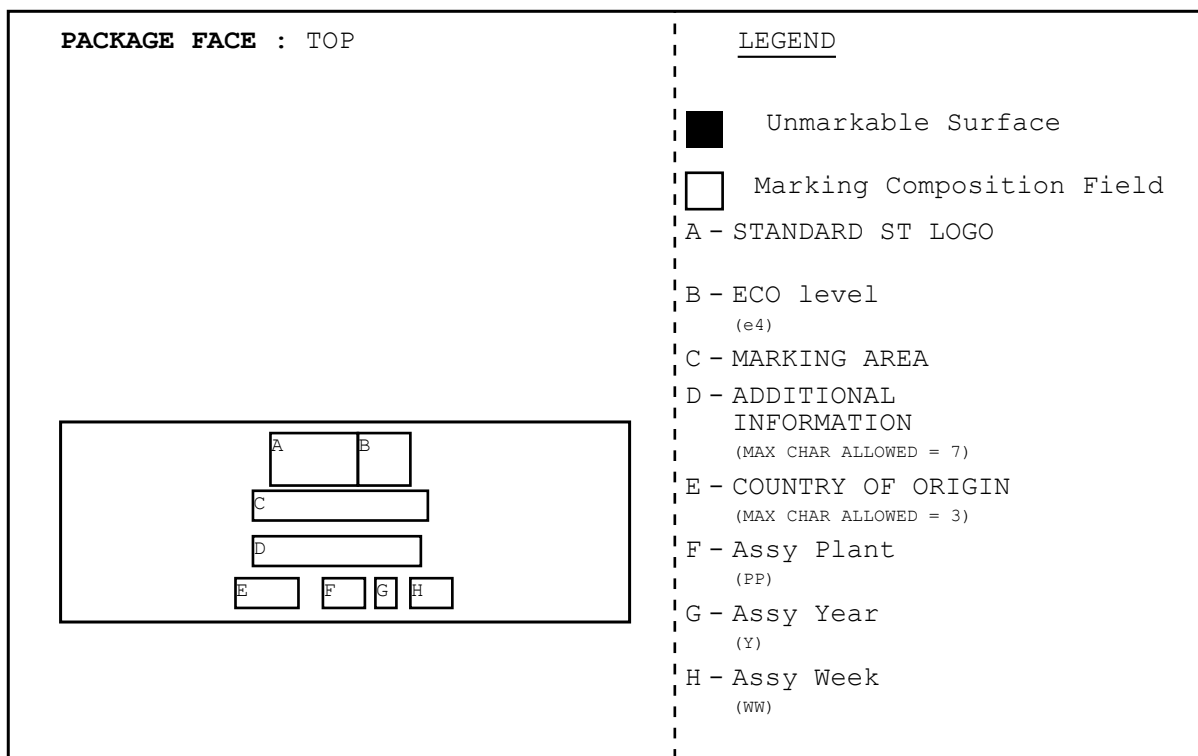
00418521_2

Table 9. B2 mechanical data

Symbol	Millimetres		
	Min	Typ	Max
A	12.57	12.7	12.83
B	9.65	9.78	9.91
C	20.44	20.57	20.70
D	19.31	19.44	19.57
E	9.27	9.40	9.53
F	3.23	3.61	3.99
G	1.44	1.57	1.70
H	19.68	19.81	19.94
I	4.70	4.83	4.96
L	0.07	0.10	0.15
M	0.89	1.02	1.15
CH1		2.72	
R		0.51	

5.2 Marking information

Figure 5. Marking composition



GADG040220211644GT

Revision history

Table 10. Document revision history

Date	Version	Changes
20-Jul-2020	1	Initial release
14-Apr-2021	2	Updated Features, Description and Device summary in cover page. Updated Table 1. Absolute maximum ratings ($T_C = 25\text{ }^{\circ}\text{C}$). and Table 3. ESD protection. Updated Table 4. Static and Table 5. Dynamic. Updated Figure 1. Power gain and drain efficiency vs output power (1440 to 1470 MHz). Updated Table 8. Components list. Added Section 5.2 Marking information. Minor text changes.

Contents

1	Electrical ratings	2
2	Electrical characteristics	3
3	Typical performances	4
3.1	Pulsed CW performance	4
3.2	WCDMA performance	4
4	Test circuits	5
5	Package information	8
5.1	B2 package information	8
5.2	Marking information	10
	Revision history	11

IMPORTANT NOTICE – PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. For additional information about ST trademarks, please refer to www.st.com/trademarks. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2021 STMicroelectronics – All rights reserved

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[STMicroelectronics:](#)

[RF2L16180CF2](#)